

-2-

ONS00470  
10/773,853Amendments to the Claims

Please amend the claims as follows:

Claims 1-9 (cancelled)

10. (previously presented): A process for forming an integrated circuit device including the steps of:

removing a portion of material from a semiconductor layer to form a tub region having a lower surface while leaving another of material within the tub region for form a matrix of isolated shapes protruding from the lower surface, wherein the matrix of shapes comprises offset rows; and

forming a dielectric region with the matrix of shapes.

11. (currently amended) The process of claim 10 wherein the step of ~~forming the tub region includes forming a tub region with~~ a removing includes removing a portion of material from the semiconductor layer to form the tub region having the lower surface while leaving another portion of material within the tub region to form a matrix of squares.

12. (original) The process of claim 10 wherein the step of forming the dielectric region includes oxidizing the matrix of shapes.

13. (original) The process of claim 12 wherein the step of oxidizing forms a nearly continuous silicon oxide tub.

14. (original) The process of claim 10 further comprising the step of forming a passive component over the dielectric region.

15. (currently amended) The process of claim 10 further comprising the step of forming an isolation trench ~~in the region in another portion of semiconductor layer material.~~

-3-

ONS00470  
10/773,853

16. (original). The process of claim 10 further comprising the steps of:

forming a dielectric layer on sidewalls of the matrix of shapes; and

forming a polycrystalline semiconductor layer over the dielectric layer.

17. (currently amended) The process of claim 10 wherein the step of ~~forming tub region includes forming tub region having removing includes removing a portion of material from the~~ semiconductor layer to form the tub region having the lower surface while leaving another portion of material within the tub region to form the matrix of shapes protruding from the lower surface, a matrix of shapes wherein shapes in a first row have a first spacing, and wherein the shapes in the first row have a second spacing from shapes in a second row, and wherein the second spacing is less than the first spacing.

18. (currently amended): A semiconductor device comprising:  
a region of semiconductor material; and  
a dielectric tub formed in the region of semiconductor material, wherein the dielectric tub includes a matrix of passivated shapes protruding from a lower surface of the dielectric tub, and wherein ~~[[as]]~~ at least some shapes are non-connected and are laterally surrounded by passivation material, and wherein adjacent rows of passivated shapes are offset.

19. (original): The device of claim 18 wherein the dielectric tub comprises oxidized silicon shapes.

20. (original): The device of claim 18 wherein the dielectric tub includes a boundary having a recessed portion.